

B3, cont substituents selected from the group consisting of optionally substituted naphthyl, optionally substituted thienyl and pentafluorophenyl, or 2) a non-ionic oxime sulfonate compound or a non-ionic N-oxyimidosulfonate compound.

27. (amended) A method for forming a photoresist relief image on a substrate comprising:

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- (a) applying a coating layer of a photoresist composition of claim 13 on a substrate;
 - and
 - (b) exposing the photoresist coating layer to patterned activating radiation and developing the exposed photoresist layer to provide a relief image.

31. (amended) An article of manufacture having on at least one surface a coating layer of the photoresist composition of claim 13.


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32. (amended) An article of manufacture comprising a microelectronic wafer or flat panel display substrate that has on at least one surface a coating layer of a photoresist of claim 13.

REMARKS

The specification has been amended to include the priority claim. For the sole purpose of reducing initial filing fees, claims 14-26, 28 and 34 have been cancelled without prejudice, and claims 3, 4-8, 10-13, 27, 31 and 32 have been amended to eliminate multiple dependencies and correct typographical matters.

Early consideration and allowance of the application are solicited.



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VERSION WITH CHANGES MARKED

3. (amended) The method of claim 1 [or 2] wherein the sensitizer is an aromatic compound.
4. (amended) The method of claim 1 [any one of claims 1 through 3] wherein the sensitizer is a carbocyclic aryl compound.
5. (amended) The method of claim 1 [any one of claims 1 through 4] wherein the sensitizer is a heteroaromatic compound.
6. (amended) The method of claim 1 [any one of claims 1 through 5] wherein the sensitizer has from 1 to 3 separate or fused rings.
7. (amended) The method of claim 1 [any one of claims 1 through 6] wherein the photoacid generator compound is an onium compound or a non-ionic compound.
8. (amended) The method of claim 1 [any one of claims 1 through 7] wherein the photoacid generator compound is an iodonium or sulfonium photoacid generator compound which has one or more cation substituents selected from the group consisting of optionally substituted naphthyl, optionally substituted thienyl and pentafluorophenyl.
10. (amended) The method of claim 1 [any one of claims 1 through 9] wherein the photoacid generator compound is a non-ionic oxime sulfonate compound or a non-ionic N-oxyimidosulfonate compound.

12. (amended) The method of claim 1 [any one of claims 1 through 11] wherein the photoresist coating layer is exposed to radiation having a wavelength of about 193 nm.

27. (amended) A method for forming a photoresist relief image on a substrate comprising:

- (a) applying a coating layer of a photoresist composition of claim 13 [any one of claims 13 through 26] on a substrate; and
- (b) exposing the photoresist coating layer to patterned activating radiation and developing the exposed photoresist layer to provide a relief image.

31. (amended) An article of manufacture having on at least one surface a coating layer of the photoresist composition of claim 13 [any one of claims 13 through 26].

32. (amended) An article of manufacture comprising a microelectronic wafer or flat panel display substrate that has on at least one surface a coating layer of a photoresist of claim 13 [any one of claims 13 through 26].